

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

Claims 1-37 (Canceled).

38. (Previously Presented) A method for fabricating a MOS device having a gate width of less than 0.3 micron, comprising:

- (a) forming an interfacial layer on a semiconductor substrate;
- (b) forming a high dielectric constant layer on the interfacial layer, the high dielectric constant layer comprising $Ta_2(O_{1-x}N_x)_5$ wherein x ranges from greater than 0 to 0.6, and wherein the interfacial layer separates the high dielectric constant layer from the substrate;
- (c) forming a gate electrode of an electrically conductive material on the high dielectric constant layer; and
- (d) forming source and drain regions in the substrate adjacent to the gate electrode.

39. (Previously Presented) The method of Claim 38 wherein the interfacial layer comprises silicon oxide, silicon nitride, or silicon oxynitride.

40. (Previously Presented) A method for fabricating a MOS device having a gate width of less than 0.3 micron, comprising:

- (a) forming an interfacial layer on a semiconductor substrate;
- (b) forming a high dielectric constant layer on the interfacial layer, the high dielectric constant layer comprising a solid solution of $(Ta_2O_5)_t-(ZrO_2)_{1-t}$ wherein t ranges from about 0.9 to less than 1, and wherein the interfacial layer separates the high dielectric constant layer from the substrate;
- (c) forming a gate electrode of an electrically conductive material on the high dielectric constant layer; and
- (d) forming source and drain regions in the substrate adjacent to the gate electrode.

41. (Previously Presented) The method of Claim 40 wherein the interfacial layer comprises silicon oxide, silicon nitride, or silicon oxynitride.

42. (Previously Presented) A method for fabricating a MOS device having a gate width of less than 0.3 micron, comprising:

- (a) forming an interfacial layer on a semiconductor substrate;
- (b) forming a high dielectric constant layer on the interfacial layer, the high dielectric constant layer comprising a solid solution of $(Ta_2O_5)_u-(HfO_2)_{1-u}$ wherein u ranges

from about 0.9 to less than 1, and wherein the interfacial layer separates the high dielectric constant layer from the substrate;

- (c) forming a gate electrode of an electrically conductive material on the high dielectric constant layer; and
- (d) forming source and drain regions in the substrate adjacent to the gate electrode.

43. (Previously Presented) The method of Claim 42 wherein the interfacial layer comprises silicon oxide, silicon nitride, or silicon oxynitride.

44. (Currently Amended) A method for fabricating a MOS device having a gate width of less than 0.3 micron, comprising:

- (a) forming a silicon nitride interfacial layer on a semiconductor substrate;
- (b) forming a high dielectric constant layer on the silicon nitride interfacial layer, the high dielectric constant layer comprising a material that is selected from the group consisting of Ta₂O₅, a solid solution of (Ta₂O₅)_r-(TiO₂)_{1-r} wherein r ranges from about 0.9 to 1, a solid solution (Ta₂O₅)_s-(Al₂O₃)_{1-s} wherein s ranges from 0.9 to less than 1, and mixtures thereof wherein the silicon nitride interfacial layer separates the high dielectric constant layer from the substrate;
- (c) forming a gate electrode of an electrically conductive material on the high dielectric constant layer; and

(d) forming source and drain regions in the substrate adjacent to the gate electrode.

45. (Previously Presented) A method for fabricating a MOS device having a gate width of less than 0.3 micron, comprising:

(a) forming an interfacial layer on a semiconductor substrate;

(b) forming a high dielectric constant layer on the interfacial layer, the high dielectric constant layer comprising a material selected from the group consisting of $Ta_2(O_{1-x}N_x)_5$ wherein x ranges from greater than 0 to 0.6, a solid solution of $(Ta_2O_5)_t-(ZrO_2)_{1-t}$ wherein t ranges from about 0.9 to less than 1, and a solid solution of $(Ta_2O_5)_u-(HfO_2)_{1-u}$ wherein u ranges from about 0.9 to less than 1,

wherein the interfacial layer separates the high dielectric constant layer from the substrate;

(c) forming a gate electrode of an electrically conductive material on the high dielectric constant layer; and

(d) forming source and drain regions in the substrate adjacent to the gate electrode.

46. (New) The method of Claim 38 wherein the interfacial layer comprises silicon oxide.

47. (New) The method of Claim 38 wherein the interfacial layer comprises silicon nitride or silicon oxynitride.

48. (New) The method of Claim 44 wherein the interfacial layer comprises silicon oxide, silicon nitride, or silicon oxynitride.

49. (New) The method of Claim 45 wherein the interfacial layer comprises silicon oxide, silicon nitride, or silicon oxynitride.